

Silicon NPN Power Transistors

2SC867

DESCRIPTION

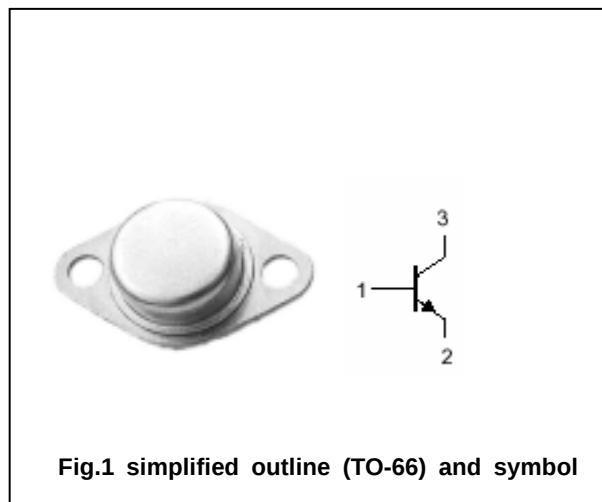
- With TO-66 package
- High collector-base breakdown voltage
: $V_{CBO}=400V(\text{min})$

APPLICATIONS

- For high voltage and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		2	A
P_D	Total power dissipation	$T_C=25$	23	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA; I_B=0$	150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1A; I_B=0.2 A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=1A; I_B=0.2 A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=0.1A; V_{CE}=3V$	50			
f_T	Transition frequency	$I_C=0.2A; V_{CE}=10V$		8		MHz

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PACKAGE OUTLINE

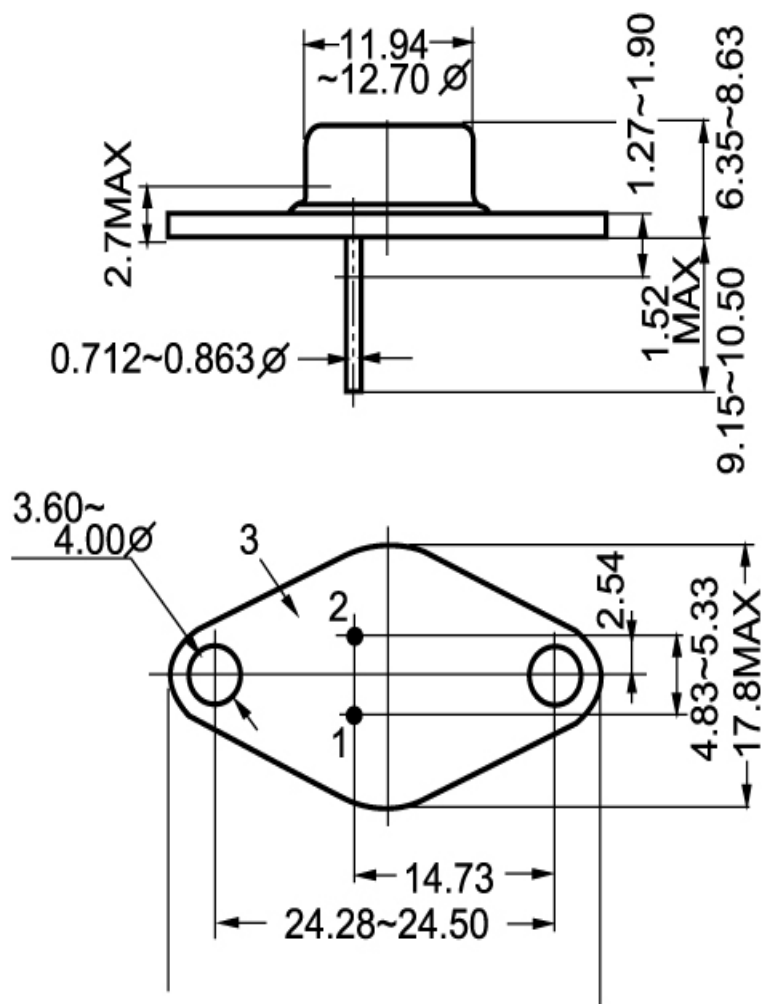


Fig.2 outline dimensions